Octal Bus Buffer

The MC74LVX541 is an advanced high speed CMOS octal bus buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74LVX541 is a noninverting type. When either $\overline{OE1}$ or $\overline{OE2}$ are high, the terminal outputs are in the high impedance state.

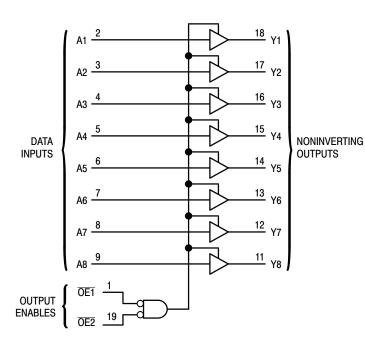
The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

- High Speed: $t_{PD} = 5.0$ ns (Typ) at $V_{CC} = 3.3$ V
- Low Power Dissipation: $I_{CC} = 4 \mu A$ (Max) at $T_A = 25^{\circ}C$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 3.6 V Operating Range
- Low Noise: $V_{OLP} = 1.2 V (Max)$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- Chip Complexity: 134 FETs or 33.5 Equivalent Gates
- ESD Performance:

Human Body Model > 2000 V; Machine Model > 200 V

• These Devices are Pb-Free and are RoHS Compliant







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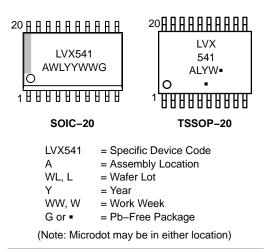
http://onsemi.com



PIN ASSIGNMENT

OE1	1●	20	Vcc
A1 [2	19	
A2 [3	18] Y1
A3 [4	17] Y2
A4 [5	16] Y3
A5 [6	15] Y4
A6 [7	14] Y5
A7 [8	13] Y6
A8 [9	12] Y7
GND [10	11] Y8

MARKING DIAGRAMS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

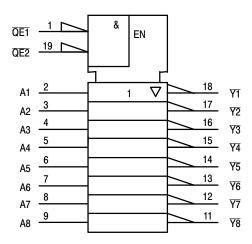


Figure 2. IEC Logic Diagram

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
V _{CC}	DC Supply Voltage		- 0.5 to + 7.0	V
V _{in}	DC Input Voltage		- 0.5 to + 7.0	V
V _{out}	DC Output Voltage	-0.5 to V _{CC} + 0.5	V	
I _{IK}	Input Diode Current	- 20	mA	
I _{OK}	Output Diode Current	± 20	mA	
l _{out}	DC Output Current, per Pin		± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins		± 50	mA
P _D	Power Dissipation in Still Air, SOIC Packages† TSSOP Package†		500 450	mW
T _{stg}	Storage Temperature		– 65 to + 150	°C

FUNCTION TABLE

Inputs	Output V	
OE2	A	Output Y
L	L	L
L	Н	Н
Х	Х	Z
н	Х	Z
	OE2 L L X	L L L H X X

This device contains protection
circuitry to guard against damage
due to high static voltages or electric
fields. However, precautions must
be taken to avoid applications of any
voltage higher than maximum rated
voltages to this high-impedance cir-
cuit. For proper operation, V _{in} and
Vout should be constrained to the
range GND \leq (V _{in} or V _{out}) \leq V _{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating: SOIC Package: -7 mW/°C from 65° to 125°C

TSSOP Package: -6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	3.6	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	-40	+85	°C
t _r , t _f	Input Rise and Fall Time V_{CC} = 3.3 V ± 0.3 V	0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			Vcc	Т	A = 25°	С	T _A = -40) to 85°C	
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 3.6	1.50 2.0 2.4			1.50 2.0 2.4		V
V _{IL}	Maximum Low–Level Input Voltage		2.0 3.0 3.6			0.50 0.80 0.80		0.50 0.80 0.80	V
V _{OH}	Minimum High-Level Output Voltage $V_{in} = V_{IH}$ or V_{IL}	$I_{OH} = -50 \ \mu A$ $I_{OH} = -50 \ \mu A$ $I_{OH} = -4 \ m A$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V _{OL}	Maximum Low–Level Output Voltage $V_{in} = V_{IH}$ or V_{IL}	$I_{OL} = 50 \ \mu A$ $I_{OL} = 50 \ \mu A$ $I_{OL} = 4 \ m A$	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
l _{in}	Maximum Input Leakage Current	V _{in} = 5.5 V or GND	0 to 3.6			±0.1		±1.0	μΑ
l _{OZ}	Maximum Three-State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or } GND$	3.6			±0.2 5		±2.5	μΑ
I _{CC}	Maximum Quiescent Supply Current	$V_{in} = V_{CC} \text{ or } GND$	3.6			4.0		40.0	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0 ns)

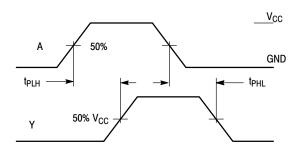
				Т	A = 25°	c	$T_{A} = -40$) to 85°C	
Symbol	Parameter	Test Cond	litions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to Y	V _{CC} = 2.7 V	C _L = 15 pF C _L = 50 pF		5.0 7.5	7.0 10.5	1.0 1.0	8.5 12.0	ns
		$V_{CC} = 3.3 \pm 0.3 V$	C _L = 15 pF C _L = 50 pF		3.5 5.0	5.0 7.0	1.0 1.0	6.0 8.0	
t _{PZL} , t _{PZH}	Output Enable Time, OE to Y	$V_{CC} = 2.7 V$ $R_L = 1 k\Omega$	C _L = 15 pF C _L = 50 pF		6.8 9.3	10.5 14.0	1.0 1.0	12.5 16.0	ns
		V_{CC} = 3.3 ± 0.3 V R _L = 1 k Ω	C _L = 15 pF C _L = 50 pF		4.7 6.2	7.2 9.2	1.0 1.0	8.5 10.5	
t _{PLZ} , t _{PHZ}	Output Disable Time, OE to Y	$V_{CC} = 2.7 V$ $R_L = 1 k\Omega$	C _L = 50 pF		11.2	15.4	1.0	17.5	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_{L} = 1 \text{ k}\Omega$	C _L = 50 pF		6.0	8.8	1.0	10.0	
t _{OSLH} , t _{OSHL}	Output to Output Skew	V _{CC} = 2.7 V (Note 1)	C _L = 50 pF			1.5		1.5	ns
		$V_{CC} = 3.3 \pm 0.3 V$ (Note 1)	C _L = 50 pF			1.0		1.0	ns
C _{in}	Maximum Input Capacitance				4.0	10		10	pF
C _{out}	Maximum Three–State Output Capacitance (Output in High Impedance State)				6.0				pF
					Typica	@ 25°C	C, V _{CC} = 5.	0 V	
C _{PD}	Power Dissipation Capacitance	(Note 2)				18	3		pF

Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|.
 C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC} / 8 (per bit). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}, C_L = 50 \text{ pF}, V_{CC} = 3.3 \text{ V}$)

		T _A = 25°C		
Symbol	Parameter		Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.5 0.8		V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.5 -0.8		V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

SWITCHING WAVEFORMS



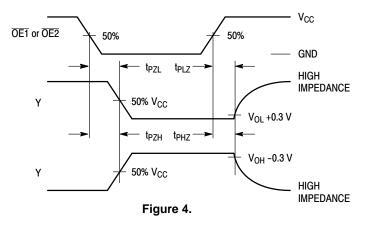
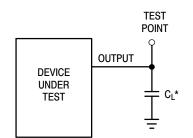


Figure 3.

TEST CIRCUITS



*Includes all probe and jig capacitance

*Includes all probe and jig capacitance Figure 5.



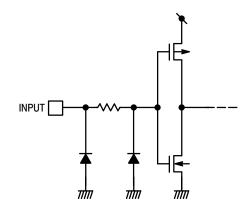


Figure 7. Input Equivalent Circuit

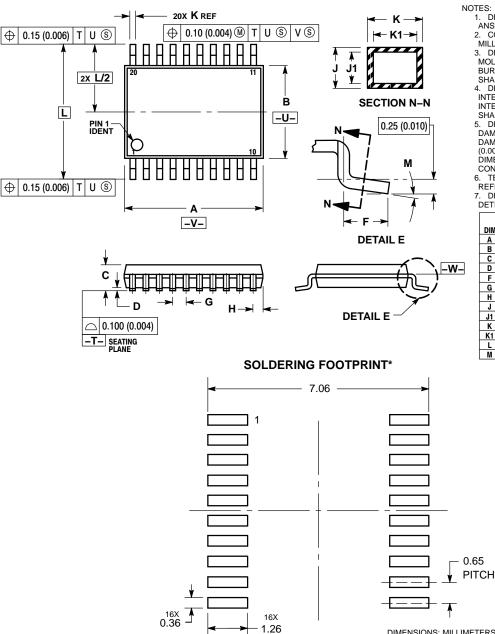
ORDERING INFORMATION

Device	Package	Shipping [†]
MC74LVX541DWG	SOIC-20 (Pb-Free)	38 Units / Rail
MC74LVX541DTR2G	TSSOP-20 (Pb-Free)	2500 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS





*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DIMENSIONS: MILLIMETERS

3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE

MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR

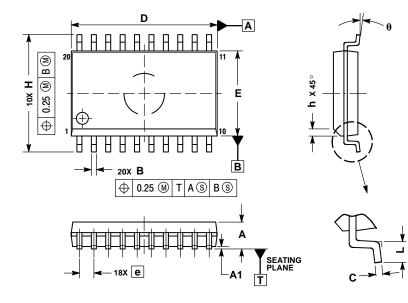
REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
Κ	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252 BSC		
Μ	0°	8°	0 °	8°	

DITES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.

PACKAGE DIMENSIONS

SOIC-20 CASE 751D-05 ISSUE G



NOTES:

- 1. DIMENSIONS ARE IN MILLIMETERS.
- 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.35	2.65			
A1	0.10	0.25			
В	0.35	0.49			
C	0.23	0.32			
D	12.65	12.95			
Ε	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	0.25	0.75			
L	0.50	0.90			
θ	0 °	7 °			

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